

<1 Ω CMOS, 1.8 V to 5.5 V, Dual SPST Switches

ADG821/ADG822/ADG823

FEATURES

0.8 Ω maximum on resistance @ 125°C 0.3 Ω maximum on resistance flatness @ 125°C 1.8 V to 5.5 V single supply 200 mA current carrying capability Automotive temperature range: -40°C to +125°C Rail-to-rail operation 8-lead MSOP 33 ns switching times Typical power consumption: <0.01 μW TTL-/CMOS-compatible inputs Pin-compatible with the ADG721/ADG722/ADG723

APPLICATIONS

Power routing Battery-powered systems Communication systems Data acquisition systems Audio and video signal routing Cellular phones Modems PCMCIA cards Hard drives Relay replacement

GENERAL DESCRIPTION

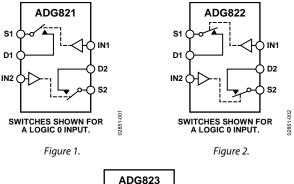
The ADG821/ADG822/ADG823 are monolithic CMOS singlepole, single-throw (SPST) switches. These switches are designed on an advanced submicron process that provides low power dissipation, yet gives high switching speed, low on resistance, and low leakage currents.

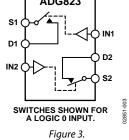
The ADG821/ADG822/ADG823 are designed to operate from a single 1.8 V to 5.5 V supply, making them ideal for use in battery-powered instruments.

Each switch of the ADG821/ADG822/ADG823 conducts equally well in both directions when on. The ADG821/ ADG822/ADG823 contain two independent SPST switches. The ADG821 and ADG822 differ only in that both switches are normally open and normally closed, respectively. In the ADG823, Switch 1 is normally open and Switch 2 is normally closed. The ADG823 exhibits break-before-make switching action.

The ADG821/ADG822/ADG823 are available in an 8-lead MSOP.

FUNCTIONAL BLOCK DIAGRAMS





PRODUCT HIGHLIGHTS

- 1. Very Low On Resistance: 0.5Ω typ.
- 2. On Resistance Flatness ($R_{FLAT(ON)}$): 0.15 Ω typ.
- 3. Automotive Temperature Range: -40°C to +125°C.
- 4. Current Carrying Capability: 200 mA.
- 5. Low Power Dissipation. CMOS construction ensures low power dissipation.
- 6. 8-Lead MSOP.

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TABLE OF CONTENTS

| Features 1 | |
|----------------------------|---|
| Applications 1 | |
| Functional Block Diagrams1 | |
| General Description 1 | |
| Product Highlights 1 | |
| Revision History 2 | |
| Specifications | , |
| Absolute Maximum Ratings5 | • |

| ESD Caution | 5 |
|---|----|
| Pin Configuration and Function Descriptions | 6 |
| Typical Performance Characteristics | 7 |
| Test Circuits | 9 |
| Terminology | 11 |
| Outline Dimensions | 12 |
| Ordering Guide | |

REVISION HISTORY

4/08—Rev. 0 to Rev. A

| Updated Format | Universal |
|----------------------------|-----------|
| Added Table 6 | |
| Updated Outline Dimensions | |
| Changes to Ordering Guide | |
| 6 6 | |

8/02—Revision 0: Initial Version

SPECIFICATIONS

 V_{DD} = 5 V \pm 10%, GND = 0 V; T_{A} = –40°C to +125°C, unless otherwise noted.

Table 1.

| Parameter | 25°C | –40°C to +85°C | -40°C to +125°C1 | Unit | Test Conditions/Comments |
|---|-------|-------------------|------------------------|---------|--|
| ANALOG SWITCH | | | | | |
| Analog Signal Range | | | 0 V to V _{DD} | V | |
| On Resistance (R _{ON}) | 0.5 | | | Ωtyp | $V_s = 0 V$ to V_{DD} , $I_s = 100 \text{ mA}$, see Figure 17 |
| | 0.6 | 0.7 | 0.8 | Ωmax | |
| On Resistance Match Between | 0.16 | | | Ωtyp | $V_s = 0 V$ to V_{DD} , $I_s = 100 \text{ mA}$ |
| Channels (ΔR _{ON}) | 0.2 | 0.25 | 0.28 | Ωmax | |
| On Resistance Flatness (R _{FLAT(ON)}) | 0.15 | | | Ωtyp | $V_{s} = 0 V \text{ to } V_{DD}$, $I_{s} = 100 \text{ mA}$ |
| | 0.23 | 0.26 | 0.3 | Ωmax | |
| LEAKAGE CURRENTS | | | | | $V_{DD} = 5.5 V$ |
| Source Off Leakage, Is (Off) | ±0.01 | | | nA typ | $V_{s} = 4.5 \text{ V}/1 \text{ V}, V_{D} = 1 \text{ V}/4.5 \text{ V}$, see Figure 18 |
| - | ±0.25 | ±3 | ±25 | nA max | |
| Drain Off Leakage, I _D (Off) | ±0.01 | | | nA typ | $V_{s} = 4.5 \text{ V}/1 \text{ V}, V_{D} = 1 \text{ V}/4.5 \text{ V}$, see Figure 18 |
| | ±0.25 | ±3 | ±25 | nA max | |
| Channel On Leakage, I _D , Is (On) | ±0.01 | | | nA typ | $V_{s} = V_{D} = 1 V$, or $V_{s} = V_{D} = 4.5 V$, see Figure 19 |
| | ±0.25 | ±3 | ±25 | nA max | |
| DIGITAL INPUTS | | | | | |
| Input High Voltage, VINH | | | 2.0 | V min | |
| Input Low Voltage, V _{INL} | | | 0.8 | V max | |
| Input Current | | | | | |
| | 0.005 | | | μA typ | $V_{IN} = V_{INL}$ or V_{INH} |
| | | | ±0.1 | µA max | |
| Digital Input Capacitance, C _{IN} | 4 | | | pF typ | |
| DYNAMIC CHARACTERISTICS ² | | | | F 9F | |
| ton | 33 | | | ns typ | $R_L = 50 \Omega$, $C_L = 35 pF$, $V_S = 3 V$, see Figure 20 |
| | 45 | 48 | 52 | ns max | ······································ |
| toff | 11 | | - | ns typ | $R_L = 50 \Omega$, $C_L = 35 pF$, $V_S = 3 V$, see Figure 20 |
| | 16 | 19 | 21 | ns max | |
| Break-Before-Make Time Delay, tBBM | 32 | | 21 | ns typ | $R_L = 50 \Omega$, $C_L = 35 pF$, $V_{51} = V_{52} = 3 V$, |
| (ADG823 Only) | 52 | | 1 | ns min | see Figure 21 |
| Charge Injection | 15 | | | pC typ | $V_s = 2.5 V$; $R_s = 0 \Omega$, $C_L = 1 nF$, see Figure 2. |
| Off Isolation | -52 | | | dB typ | $R_L = 50 \Omega$, $C_L = 5 pF$, $f = 1 MHz$, see Figure 23 |
| Channel-to-Channel Crosstalk | -82 | | | dB typ | $R_L = 50 \Omega$, $C_L = 5 pF$, $f = 1 MHz$, see Figure 24 |
| Bandwidth –3 dB | 24 | | | MHz typ | $R_L = 50 \Omega$, $C_L = 5 pF$, see Figure 25 |
| C _s (Off) | 85 | | | pF typ | f = 1 MHz |
| C_{D} (Off) | 98 | | | pF typ | f = 1 MHz |
| C_D (OII) C_D , C_s (On) | 230 | | | pF typ | f = 1 MHz |
| POWER REQUIREMENTS | 250 | | | | $V_{DD} = 5.5 \text{ V}$, digital inputs = 0 V or 5.5 V |
| | 0.001 | | | uA two | $v_{00} = 3.5 v$, aigital inputs = 0 v or 5.5 v |
| lod | 0.001 | 1.0 | 2.0 | μA typ | |
| | | 1.0 | 2.0 | μA max | |

 $^{\rm 1}$ On resistance parameters tested with $I_{\rm S}$ = 10 mA. $^{\rm 2}$ Guaranteed by design, not subject to production test.

 V_{DD} = 2.7 V to 3.6 V, GND = 0 V, T_A = -40°C to +125°C, unless otherwise noted.

Table 2.

| Parameter | 25°C | –40°C to +85°C | -40°C to +125°C1 | Unit | Test Conditions/Comments |
|--|-------|-------------------|---------------------|---------|---|
| ANALOG SWITCH | | | | | |
| Analog Signal Range | | | $0 V to V_{DD}$ | V | |
| On Resistance (R _{ON}) | 0.7 | | | Ωtyp | $V_s = 0 V$ to V_{DD} , $I_s = 100 \text{ mA}$, see Figure 17 |
| | 1.4 | 1.5 | 1.6 | Ωmax | |
| On Resistance Match Between | 0.16 | | | Ωtyp | $V_{s} = 0 V \text{ to } V_{DD}$, $I_{s} = 100 \text{ mA}$ |
| Channels (ΔR _{ON}) | 0.2 | 0.25 | 0.28 | Ωmax | |
| On Resistance Flatness (R _{FLAT(ON)}) | 0.3 | | 0.33 | Ωtyp | $V_{s} = 0 V \text{ to } V_{DD}, I_{s} = 100 \text{ mA}$ |
| LEAKAGE CURRENTS | | | | | $V_{DD} = 3.6 V$ |
| Source Off Leakage, Is (Off) | ±0.01 | | | nA typ | $V_{\rm S} = 3.3 \text{ V}/1 \text{ V}$, $V_{\rm D} = 1 \text{ V}/3.3 \text{ V}$, see Figure 18 |
| | ±0.25 | ±3 | ±15 | nA max | |
| Drain Off Leakage, I _D (Off) | ±0.01 | | | nA typ | $V_{s} = 3.3 \text{ V}/1 \text{ V}, V_{D} = 1 \text{ V}/3.3 \text{ V}$, see Figure 18 |
| | ±0.25 | ±3 | ±25 | nA max | |
| Channel On Leakage, I _D , I _S (On) | ±0.01 | | | nA typ | $V_s = V_D = 1 V$, or 3.3 V, see Figure 19 |
| | ±0.25 | ±3 | ±25 | nA max | |
| DIGITAL INPUTS | | | | | |
| Input High Voltage, V _{INH} | | | 2.0 | V min | |
| Input Low Voltage, VINL | | | 0.8 | V max | |
| Input Current | | | | | |
| I _{INL} or I _{INH} | 0.005 | | | μA typ | $V_{IN} = V_{INL}$ or V_{INH} |
| | | | ±0.1 | µA max | |
| Digital Input Capacitance, C _{IN} | 4 | | | pF typ | |
| DYNAMIC CHARACTERISTICS ² | | | | | |
| ton | 48 | | | ns typ | $R_L = 50 \Omega$, $C_L = 35 pF$, $V_S = 1.5 V$, see Figure 20 |
| | 67 | 74 | 78 | ns max | |
| toFF | 12 | | | ns typ | $R_{L} = 50 \Omega$, $C_{L} = 35 pF$, $V_{S} = 1.5 V$, see Figure 20 |
| | 18 | 20 | 23 | ns max | |
| Break-Before-Make Time Delay, t _{BBM} | 40 | | | ns typ | $R_L = 50 \Omega$, $C_L = 35 pF$, $V_{S1} = V_{S2} = 1.5 V$, |
| (ADG823 Only) | | | 1 | ns min | see Figure 21 |
| Charge Injection | ±2 | | | pC typ | $V_{s} = 1.5 V; R_{s} = 0 \Omega, C_{L} = 1 nF, see Figure 22$ |
| Off Isolation | -52 | | | dB typ | $R_L = 50 \Omega$, $C_L = 5 pF$, $f = 1 MHz$, see Figure 23 |
| Channel-to-Channel Crosstalk | -82 | | | dB typ | $R_L = 50 \Omega$, $C_L = 5 pF$, $f = 1 MHz$, see Figure 24 |
| Bandwidth –3 dB | 24 | | | MHz typ | $R_L = 50 \Omega$, $C_L = 5 pF$, see Figure 25 |
| C _s (Off) | 85 | | | pF typ | f = 1 MHz |
| C _D (Off) | 98 | | | pF typ | f = 1 MHz |
| C_D, C_S (On) | 230 | | | pF typ | f = 1 MHz |
| POWER REQUIREMENTS | | | | 1 .71: | $V_{DD} = 3.6$ V, digital inputs = 0 V or 3.6 V |
| | 0.001 | | | μA typ | |
| .00 | 0.001 | 1.0 | 2.0 | μA max | |

 $^{\rm 1}$ On resistance parameters tested with $l_{\rm S}$ = 10 mA. $^{\rm 2}$ Guaranteed by design, not subject to production test.

ABSOLUTE MAXIMUM RATINGS

 $T_A = 25^{\circ}C$, unless otherwise noted.

Table 3.

| Parameter | Rating |
|---|--|
| V _{DD} to GND | –0.3 V to +7 V |
| Analog Inputs ¹ | -0.3 V to V _{DD} + 0.3 V or 30 mA, whichever occurs first |
| Digital Inputs ¹ | -0.3 V to V _{DD} + 0.3 V or 30 mA, whichever occurs first |
| Peak Current, S or D | 400 mA (pulsed at 1 ms, 10% duty cycle maximum) |
| Continuous Current, S or D | 200 mA |
| Operating Temperature Range | |
| Automotive | –40°C to +125°C |
| Storage Temperature Range | –65°C to +150°C |
| Junction Temperature (TJ max) | 150°C |
| Package Power Dissipation | $(T_J max - T_A)/\theta_{JA}$ |
| 8-Lead MSOP Thermal Impedance | |
| θ _{JA} | 206°C/W |
| θ」 | 44°C/W |
| Lead Temperature, Soldering (10 sec) | 300°C |
| IR Reflow, Peak Temperature (<20 sec) | 235℃ |

¹ Overvoltages at IN, S, or D are clamped by internal diodes. Current should be limited to the maximum ratings given.

Stresses above those listed under Absolute Maximum Ratings may cause permanent damage to the device. This is a stress rating only; functional operation of the device at these or any other conditions above those indicated in the operational section of this specification is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

Table 4. Truth Table for the ADG821/ADG822

| ADG821 INx | ADG822 INx | Switch x Condition |
|------------|------------|--------------------|
| 0 | 1 | Off |
| 1 | 0 | On |

Table 5. Truth Table for the ADG823

| IN1 | IN2 | Switch S1 | Switch S2 |
|-----|-----|-----------|-----------|
| 0 | 0 | Off | On |
| 0 | 1 | Off | Off |
| 1 | 0 | On | On |
| 1 | 1 | On | Off |

ESD CAUTION



ESD (electrostatic discharge) sensitive device. Charged devices and circuit boards can discharge without detection. Although this product features patented or proprietary protection circuitry, damage may occur on devices subjected to high energy ESD. Therefore, proper ESD precautions should be taken to avoid performance degradation or loss of functionality.

PIN CONFIGURATION AND FUNCTION DESCRIPTIONS

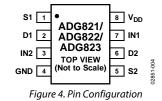
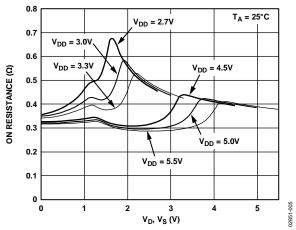


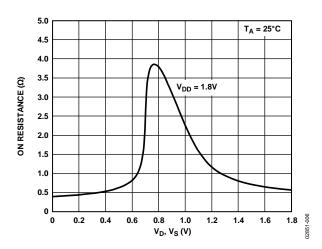
Table 6. Pin Function Descriptions

| Pin No. | Mnemonic | Description |
|---------|-----------------|--|
| 1 | S1 | Source Terminal. This pin can be an input or output. |
| 2 | D1 | Drain Terminal. This pin can be an input or output. |
| 3 | IN2 | Logic Control Input. |
| 4 | GND | Ground (0 V) Reference. |
| 5 | S2 | Source Terminal. This pin can be an input or output. |
| б | D2 | Drain Terminal. This pin can be an input or output. |
| 7 | IN1 | Logic Control Input. |
| 8 | V _{DD} | Most Positive Power Supply Potential. |



TYPICAL PERFORMANCE CHARACTERISTICS

Figure 5. On Resistance vs. V_D, V_s





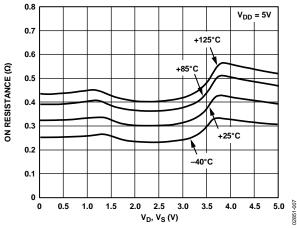


Figure 7. On Resistance vs. V_D , V_S for Different Temperatures, $V_{DD} = 5 V$

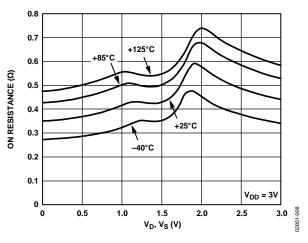


Figure 8. On Resistance vs. V_D , V_S for Different Temperatures, $V_{DD} = 3 V$

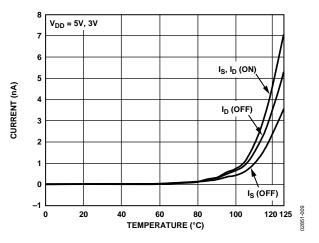


Figure 9. Leakage Current vs. Temperature

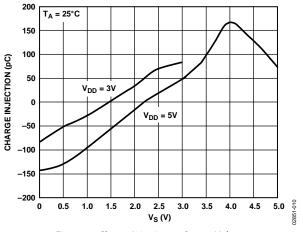
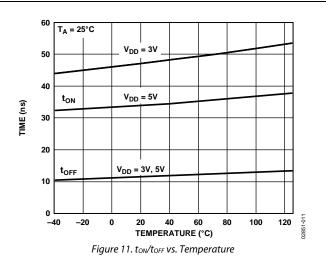
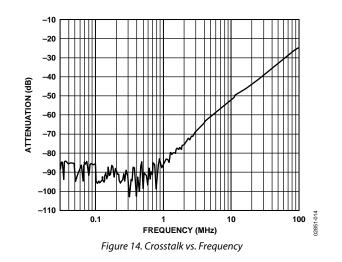
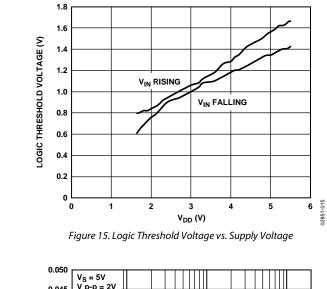


Figure 10. Charge Injection vs. Source Voltage

0







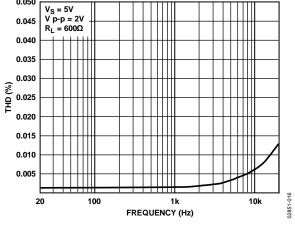
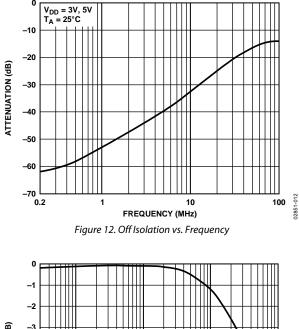


Figure 16. THD vs. Frequency



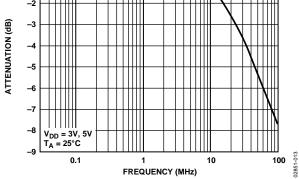
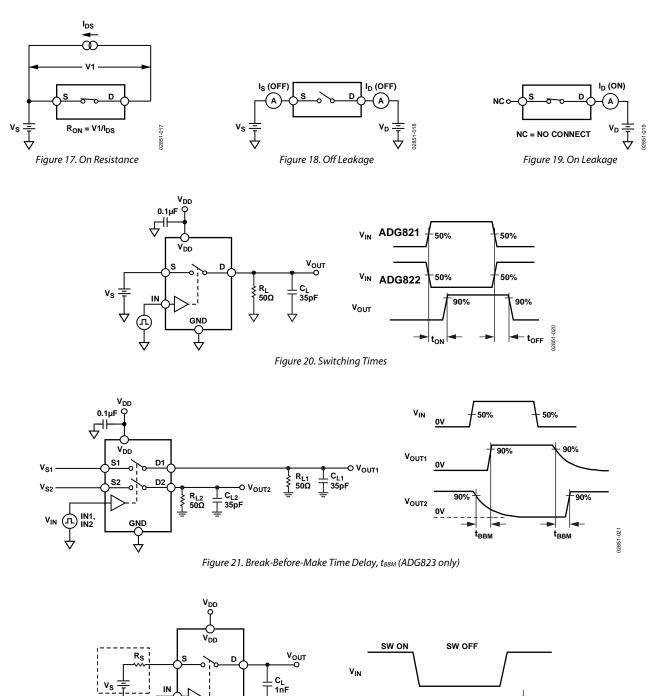


Figure 13. On Response vs. Frequency

TEST CIRCUITS



Vout

GND

4 V

(л

Δνουτ

02851-022

 $\mathbf{Q}_{\mathsf{INJ}} = \mathbf{C}_{\mathsf{L}} \times \Delta \mathbf{V}_{\mathsf{OUT}}$

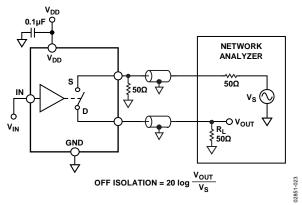


Figure 23. Off Isolation

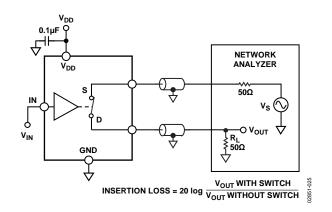
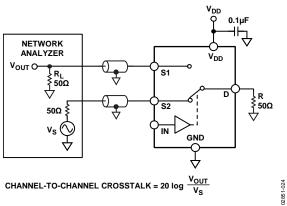


Figure 25. Bandwidth



V_{OUT} Vs CHANNEL-TO-CHANNEL CROSSTALK = 20 log

Figure 24. Channel-to-Channel Crosstalk

TERMINOLOGY

VDD

Most positive power supply potential.

GND

Ground (0 V) reference.

IDD Positive supply current.

S

Source terminal. May be an input or output.

D

Drain terminal. May be an input or output.

IN Logic control input.

R_{ON} Ohmic resistance between Terminal D and Terminal S.

 ΔR_{ON}

On resistance match between any two channels (that is, $R_{ON} max - R_{ON} min$).

R_{FLAT}(ON)

Flatness is defined as the difference between the maximum and minimum value of on resistance as measured over the specified analog signal range.

Is (Off) Source leakage current with the switch off.

 $I_{D} \mbox{ (Off)} \label{eq:ID} \mbox{Drain leakage current with the switch off.}$

I_D, I_S (On) Channel leakage current with the switch on.

 $\mathbf{V}_{D}, \mathbf{V}_{S}$ Analog voltage on Terminal D and Terminal S.

 \mathbf{V}_{INL} Maximum input voltage for Logic 0.

 \mathbf{V}_{INH} Minimum input voltage for Logic 1. I_{INL} (I_{INH}) Input current of the digital input.

Cs (Off) Off switch source capacitance.

C_D (Off) Off switch drain capacitance.

C_D, C_s (On) On switch capacitance.

ton

Delay between applying the digital control input and the output switching on.

t_{OFF} Delay between applying the digital control input and the output switching off.

t_{BBM}

Off time or on time measured between the 90% points of both switches, when switching from one address state to another.

Charge Injection

Charge injection is a measure of the glitch impulse transferred from the digital input to the analog output during switching.

Crosstalk

Crosstalk is a measure of unwanted signal that is coupled through from one channel to another as a result of parasitic capacitance.

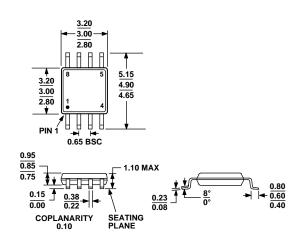
Off Isolation A measure of unwanted signal coupling through an off switch.

Bandwidth The frequency at which the output is attenuated by -3 dBs.

On Response The frequency response of the on switch.

Insertion Loss The loss due to the on resistance of the switch.

OUTLINE DIMENSIONS



COMPLIANT TO JEDEC STANDARDS MO-187-AA Figure 26. 8-Lead Mini Small Outline Package [MSOP] (RM-8) Dimensions shown in millimeters

ORDERING GUIDE

| Model | Temperature Range | Package Description | Package Option | Branding |
|-------------------------|-------------------|--|----------------|----------|
| ADG821BRM | -40°C to +125°C | 8-Lead Mini Small Outline Package [MSOP] | RM-8 | SQB |
| ADG821BRM-REEL | -40°C to +125°C | 8-Lead Mini Small Outline Package [MSOP] | RM-8 | SQB |
| ADG821BRMZ ¹ | -40°C to +125°C | 8-Lead Mini Small Outline Package [MSOP] | RM-8 | SOP |
| ADG821BRMZ-REEL71 | -40°C to +125°C | 8-Lead Mini Small Outline Package [MSOP] | RM-8 | SOP |
| ADG822BRM | -40°C to +125°C | 8-Lead Mini Small Outline Package [MSOP] | RM-8 | SRB |
| ADG822BRM-REEL | -40°C to +125°C | 8-Lead Mini Small Outline Package [MSOP] | RM-8 | SRB |
| ADG822BRM-REEL7 | -40°C to +125°C | 8-Lead Mini Small Outline Package [MSOP] | RM-8 | SRB |
| ADG822BRMZ ¹ | -40°C to +125°C | 8-Lead Mini Small Outline Package [MSOP] | RM-8 | S1J |
| ADG822BRMZ-REEL71 | -40°C to +125°C | 8-Lead Mini Small Outline Package [MSOP] | RM-8 | S1J |
| ADG823BRM | -40°C to +125°C | 8-Lead Mini Small Outline Package [MSOP] | RM-8 | SSB |
| ADG823BRM-REEL | -40°C to +125°C | 8-Lead Mini Small Outline Package [MSOP] | RM-8 | SSB |
| ADG823BRMZ ¹ | -40°C to +125°C | 8-Lead Mini Small Outline Package [MSOP] | RM-8 | SSB# |
| ADG823BRMZ-REEL71 | -40°C to +125°C | 8-Lead Mini Small Outline Package [MSOP] | RM-8 | SSB# |

¹ Z = RoHS Compliant Part, # denotes RoHS compliant product may be top or bottom marked.

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